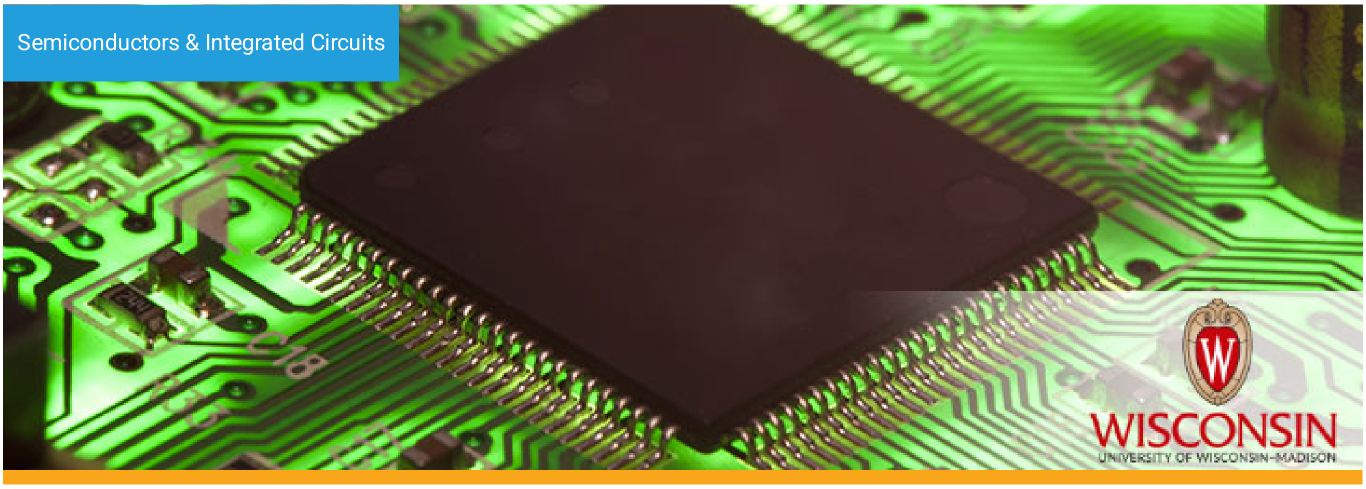

Flexible Transistors With Near-Junction Heat Dissipation

View U.S. Patent No. 11,495,512 in PDF format.

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The Invention

Flexible transistors and electronic circuits incorporating the transistors are provided. The flexible transistors promote heat dissipation from the active regions of the transistors while preserving their mechanical flexibility and high-frequency performance. The transistor designs utilize thru-substrate vias (TS Vs) beneath the active regions of thin-film type transistors on thin flexible substrates. To promote rapid heat dissipation, the TSVs are coated with a material having a high thermal conductivity that transfers heat from the active region of the transistor to a large-area ground.

Additional Information

For More Information About the Inventors

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Tech Fields

- Semiconductors & Integrated Circuits : Design & fabrication

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846